



CP 2812

PATENT
29926/37960

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

CHO et al.

Serial No. 10/054,520

Filed: January 22, 2002

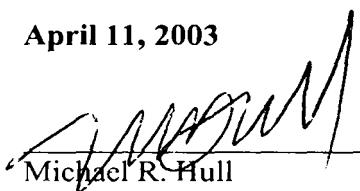
For: METHOD OF FORMING
MEMORY DEVICE

Group Art Unit: 2812

Examiner: Not Yet Assigned

) I hereby certify that this paper is being
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April 11, 2003



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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
Washington, DC 20231

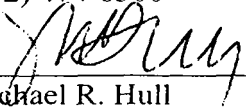
Sir:

The patents listed on the enclosed PTO/SB/08 are submitted pursuant to
37 C.F.R. § 1.56, § 1.97 and § 1.98. Copies of the patents are enclosed as necessary.
This information disclosure statement is being filed, to the best of the undersigned's
knowledge, before the mailing date of a first Office action on the merits. In
accordance with 37 CFR §1.97(b), no certification or fee is required.

Respectfully submitted,

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Atty. Docket No.

29926/37960

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Filing Date

01/22/2002

Group Art Unit

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INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

FOREIGN PATENT DOCUMENTS

*Examiner Initials		Document Number	Publication Date	Country	Class	Subclass	Translation	
							Yes	No
	B01	KR 2001-37680	05/15/2001	Korea			Abstract	

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



KR Laid-Open No. 2001-37680

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Capacitor and method for forming the same

This invention relates to a method for forming a capacitor in a semiconductor device; and, more particularly, to a method for forming a capacitor with use of a simplified process. A TiN layer or any metal layer to which a chemical vapor deposition (CVD) technique can be applied is used for the lower electrode of the capacitor. A dielectric layer uses Al_2O_3 , and a polysilicon layer or a metal layer is used as an upper electrode of the capacitor. Also, the capacitor is formed in a cylinder shape; however, the lower electrode is directly contacted to a landing pad without a contact plug. As a result of this direct contact, it is possible to simplify a process as well as to obtain a required capacitance even in a minimum area.